# Epitaxial Growth GaAs on Silicon

#### Why?

Large area wafers not available with GaAs GaAs expensive

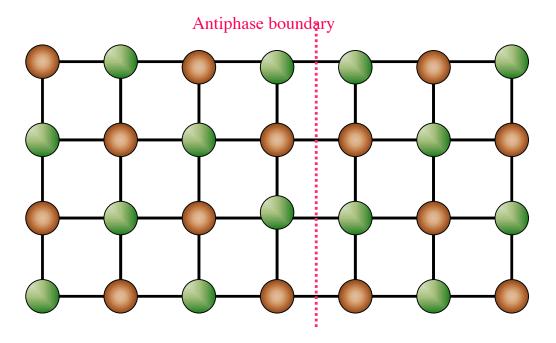




Some Materials Science Problems

Antiphase boundaries
GaAs/Si interphase electrically charged
Autodoping
Lattice mismatch
SiO<sub>2</sub> surface

# What are antiphases?

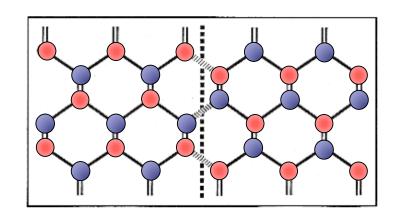


Why do they naturally occur in GaAs when grown on Si?

Why are they harmful?

#### Antiphases: Why harmful

GaAs antiphase domain (two fcc)

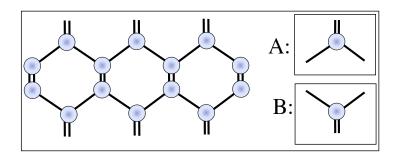


Ga-As bond neutral 3/4+5/4 el pr bond = 2 Ga-Ga bonds neutral 3/4+3/4, paired bond 2, accept 1/2 el As-As bonds donors gives off 1/2 electronic charge

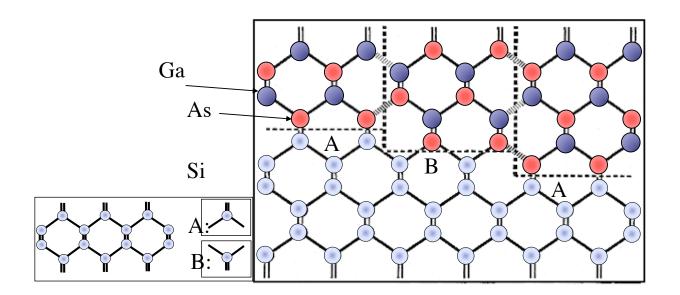
Scattering of electrons, lower mobility (harmful for FET) recombination centers harmful for optoelectronic devices

## Antiphases: Why natural on Si?

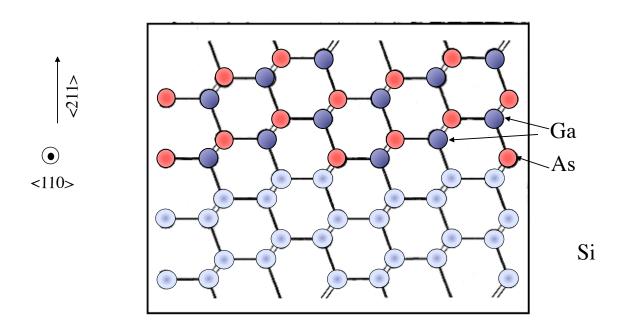
Si -two sublattices (two fcc )

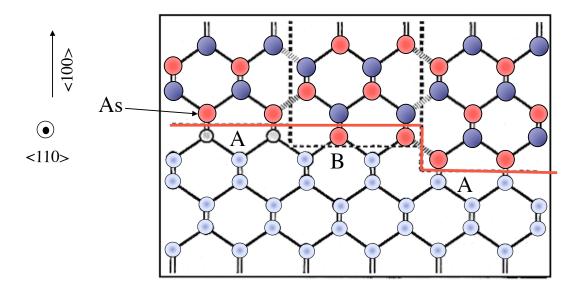


# Antiphases: Why natural on Si? 2

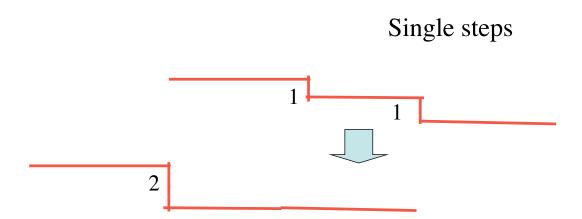


The (211) surface No Antiphases:

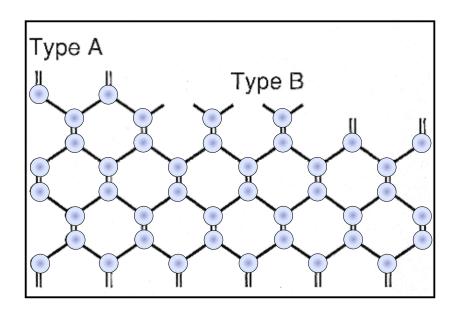




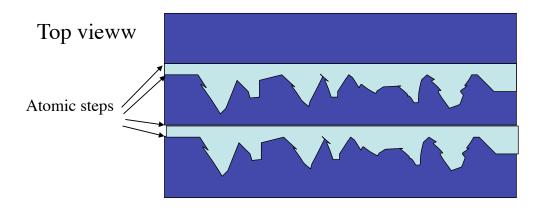
So if only had double steps - then fine



Is it possible to make only double steps?

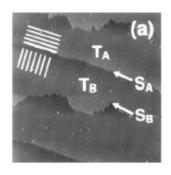


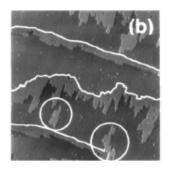
Type A lower energy than B, It IS possible to make only steps typ A

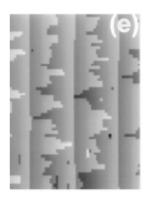


Type A lower energy than B, It is possible to make only steps typ A

#### STM \*Scanning tunneling micrographs)







Type A lower energy than B, It is possible to make only steps typ A

Bert Voigtländer et al PRB 78, 2164 (1997)